

environment of the projection optical system and the change amount of the image formation characteristics for each condition based on a result of the detection.

2. (Amended) The adjustment method for a projection optical system according to Claim 1, wherein when the installation environment of the projection optical system changes, the image formation characteristics of the projection optical system is adjusted based on the predetermined relationship.

3. (Amended) The adjustment method for a projection optical system according to Claim 2, wherein the image formation characteristics of the projection optical system are adjusted by changing the wavelength of the illumination light based on the predetermined relationship.

4. (Amended) An adjustment method for a projection optical system which projects an image of a pattern on a first surface onto a second surface, comprising:

changing the wavelength of the illumination light for illuminating the pattern on the first surface according to the installation environment of the relocated location in advance when assembling and adjusting the projection optical system at the assembly location in case that installation environment is different between an assembly location where the projection optical system is assembled and adjusted and a relocated location where the projection optical system is used.

5. (Amended) The adjustment method for a projection optical system according to Claim 2, wherein gas whose barometric pressure changes in association with the atmospheric pressure is supplied inside the projection optical system, and the change of the installation

environment of the projection optical system is the change of the atmospheric pressure.

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6. (Amended) The adjustment method for a projection optical system according to Claim 1, wherein the predetermined relationship is determined based on the first relationship between the change amount of the installation environment and the change amount of the wavelength, and the second relationship between the change amount of the wavelength and the change amount of the image formation characteristics.

7. (Amended) The adjustment method for a projection optical system according to Claim 6, wherein the first relationship is determined based on the refractive index characteristics of the glass material of the projection optical system and the refractive index characteristics of gas around the projection optical system.

8. (Amended) The adjustment method for a projection optical system according to Claim 7, wherein the projection optical system is comprised of a plurality of types of glass materials, and the first relationship is determined by equalizing the relationship between the change amount of the installation environment and the change amount of the wavelength determined for each one of the plurality of types of glass materials.

10. (Amended) The adjustment method for a projection optical system according to Claim 1, wherein the change amount of the image formation characteristics due to the change of the wavelength of the illumination light is detected in a state where the installation environment of the projection optical system is maintained to be constant.

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11. (Amended) The adjustment method for a projection optical system according to Claim 4, wherein the wavelength of the illumination light when the projection optical system is used in the relocated location is set to a wavelength according to the installation environment of the assembly location.

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12. (Amended) An exposure method for illuminating a pattern formed on a first surface by an illumination light and projecting an image of the pattern onto a second surface via a projection optical system, comprising:

a first step of determining information on a change amount of predetermined image formation characteristics of the projection optical system; and

a second step of correcting the change amount of the predetermined image formation characteristics using a first technique for adjusting the predetermined image formation characteristics by changing a wavelength of the illumination light and a second technique for adjusting the predetermined image formation characteristics using a method different from the first technique.

13. (Amended) The exposure method according to Claim 12, wherein in the first step, the change amount of the predetermined image formation characteristics is determined based on the result of measurement of the installation environment of the projection optical system.

14. (Amended) The exposure method according to Claim 13, wherein the change amount of the installation environment is the difference between the measured environment and a predetermined reference environment.

15. (Amended) The exposure method according to Claim 12, wherein the second technique is the adjustment of the projection optical system.

16. (Amended) The exposure method according to Claim 15, wherein the adjustment of the projection optical system is performed by a first adjustment for moving at least one lens of the projection optical system in the optical axis direction of the projection optical system or inclining the lens with respect to the optical axis, or by a second adjustment for controlling the barometric pressure in a space sealed between a predetermined part of lenses of the projection optical system.

17. (Amended) The exposure method according to Claim 12, wherein in the first step, the change amount of the predetermined image formation characteristics caused by a factor other than the installation environment of the projection optical system is determined.

18. (Amended) The exposure method according to Claim 17, wherein the change amount of the predetermined image formation characteristics caused by a factor other than the installation environment includes the fluctuation of the predetermined image formation characteristics due to the irradiation of the illumination light.

19. (Amended) The exposure method according to Claim 12, wherein the projection optical system is comprised of a plurality of types of glass materials.

20. (Amended) The exposure method according to Claim 19, wherein in the second step, the residue of the change amount of the predetermined image formation characteristics which the first technique could not completely correct is corrected by the second technique after

executing the first technique.

21. (Amended) The exposure method according to Claim 13, wherein when the change amount of the installation environment is a predetermined value or more, the change amount of the predetermined image formation characteristics is corrected using the first technique in the second step.

22. (Amended) An exposure method using a projection exposure apparatus for illuminating a pattern formed on a first surface by an illumination light and projecting an image of the pattern onto a second surface via a projection optical system, comprising:

measuring an installation environment of the projection optical system to determine a change amount of the installation environment, and

changing a wavelength of the illumination light according to the change amount of the installation environment when the projection exposure apparatus is executing a predetermined preparation operation for projecting the image of the pattern onto the second surface.

23. (Amended) The exposure method according to Claim 22, wherein the predetermined preparation operation includes at least one operation among operations of setting a mask on which the pattern is formed at a predetermined position for exposure in the projection exposure apparatus; of setting a substrate onto which the image of the pattern is projected at a predetermined exposure position in the projection exposure apparatus, and of specifying the illumination area of the illumination light on the mask.

24. (Amended) A device manufacturing method comprising transferring the device pattern onto a work piece using the exposure method according to Claim 12.

25. (Amended) A projection exposure apparatus comprising an illumination optical system which illuminates a mask pattern by an illumination light, and a projection optical system which projects the image of the mask pattern onto a substrate, the apparatus comprising:

a wavelength adjusting device which changes a wavelength of the illumination light;

an image formation characteristics measurement system which measures a change amount of image formation characteristics of the projection optical system;

a control system which is electrically connected to the wavelength adjusting device and the image formation characteristics measurement system, changes at least one condition of illumination condition for illuminating the mask pattern and structural condition of the mask pattern in various ways, controls the formation characteristics measurement system to measure a change amount of the image formation characteristics while changing the wavelength by the wavelength adjusting device for each condition, and determines a predetermined relationship between a change amount of the installation environment of the projection optical system and the change amount of the image formation characteristics based on the measurement results for the each condition; and

a memory which is electrically connected to the control system and stores the predetermined relationship determined by the control system for the each condition.

26. (Amended) A projection exposure apparatus comprising:

an illumination optical system which illuminates a mask pattern by an illumination light;

a projection optical system which projects the image of the mask pattern onto a substrate;

a measurement device which determines information on a change amount of predetermined image formation characteristics of the projection optical system;

a first image formation characteristics adjustment system which is electrically connected to the measurement device and adjusts the predetermined image formation characteristics by a first technique for changing a wavelength of the illumination light; and

a second image formation characteristics adjustment system which is electrically connected to the measurement device and adjusts the predetermined image formation characteristics by a second technique which is different from the first technique.

27. (Amended) The projection exposure apparatus according to Claim 26, wherein the second image formation characteristics adjustment system adjusts the image formation characteristics by adjusting the projection optical system.

28. (Amended) The projection exposure apparatus according to Claim 27, wherein the projection optical system is comprised of a plurality of types of glass materials.

29. (Amended) The projection exposure apparatus according to Claim 28, wherein the second image formation characteristics adjustment system adjusts the residue of the change amount of the predetermined image formation characteristics which the first image formation characteristics adjustment system could not correct.

30. (Amended) The projection exposure apparatus according to Claim 26, wherein the measurement device determines the change amount of the installation of the projection

optical system as the information, and when the change amount of the installation environment is a predetermined value or more, the predetermined image formation characteristics are adjusted using the first image formation characteristics adjustment system.

31. (Amended) A projection exposure apparatus comprising:

an illumination optical system which illuminates a mask pattern by an illumination light;

a projection optical system which projects the image of the mask pattern onto a substrate;

a wavelength adjusting device which changes a wavelength of the illumination light;

an installation environment measurement system which measures the installation environment of the projection optical system and determines a change amount of the installation environment; and

a certain device which executes a predetermined preparation operation for projecting the image of the pattern onto the substrate;

wherein the wavelength adjusting device changes the wavelength of the illumination light according to the change amount of the installation environment when the certain device is executing the predetermined preparation operation.

32. (Amended) The projection exposure apparatus according to Claim 31, wherein the predetermined preparation operation includes at least one operation of the operations of setting the mask on which the pattern is formed at a predetermined position for exposure in the projection exposure apparatus, an operation for setting the substrate onto which the image of the pattern is projected at a predetermined exposure position in the projection exposure apparatus, and an operation for specifying an illumination area of the illumination light on the

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mask.

Please add claims 33-35 as follows:

33. The adjustment method for a projection optical system according to Claim 3 wherein gas whose barometric pressure changes in association with the atmospheric pressure is supplied inside the projection optical system, and the change of the installation environment of the projection optical system is the change of the atmospheric pressure.
34. The adjustment method for a projection optical system according to Claim 4 wherein gas whose barometric pressure changes in association with the atmospheric pressure is supplied inside the projection optical system, and the change of the installation environment of the projection optical system is the change of the atmospheric pressure.
35. A device manufacturing method comprising transferring the device pattern onto a work piece using the exposure method according to Claim 22.

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